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1	1672	118/719.ccls.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/01/09 20:14
2	2090	29/25.01.ccls.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/01/09 20:07
3	333	427/9.ccls.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/01/09 20:07
4	6936	438/5-18.ccls.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/01/09 20:07
5	2423	700/19,49,52,99-104,108-111,119-121,123.ccls.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/01/09 20:08
6	894	L1-L5	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/01/09 20:08
7	13149	118/719.ccls. or 29/25.01.ccls. or 427/9.ccls. or 438/5-18.ccls. or 700/19,49,52,99-104,108-111,119-121,123.ccls.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/01/09 20:08
8	1237213	((semiconductor or (semi adj conductor) or semi-conductor or wafer or IC or (integrated adj circuit) or lot or (micro adj electronic) or microelectronic or memory or (logic adj unit) or microprocessor) with (process\$3 or fabricat\$3 or produc\$4 or manufactur\$3 or making))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/01/09 20:39
9	7683	(118/719.ccls. or 29/25.01.ccls. or 427/9.ccls. or 438/5-18.ccls. or 700/19,49,52,99-104,108-111,119-121,123.ccls.) and (((semiconductor or (semi adj conductor) or semi-conductor or wafer or IC or (integrated adj circuit) or lot or (micro adj electronic) or microelectronic or memory or (logic adj unit) or microprocessor) with (process\$3 or fabricat\$3 or produc\$4 or manufactur\$3 or making)))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/01/09 20:40
10	1146265	((semiconductor or (semi adj conductor) or semi-conductor or wafer or IC or (integrated adj circuit) or lot or (micro adj electronic) or microelectronic or memory or (logic adj unit) or microprocessor or process\$3 or fabricat\$3 or produc\$4 or manufactur\$3) with (deposit\$3 or etch\$3 or metrology or measur\$3 or tool\$3))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/01/09 20:41
11	5313	((118/719.ccls. or 29/25.01.ccls. or 427/9.ccls. or 438/5-18.ccls. or 700/19,49,52,99-104,108-111,119-121,123.ccls.) and (((semiconductor or (semi adj conductor) or semi-conductor or wafer or IC or (integrated adj circuit) or lot or (micro adj electronic) or microelectronic or memory or (logic adj unit) or microprocessor) with (process\$3 or fabricat\$3 or produc\$4 or manufactur\$3 or making)))) and (((semiconductor or (semi adj conductor) or semi-conductor or wafer or IC or (integrated adj circuit) or lot or (micro adj electronic) or microelectronic or memory or (logic adj unit) or microprocessor or process\$3 or fabricat\$3 or produc\$4 or manufactur\$3) with (deposit\$3 or etch\$3 or metrology or measur\$3 or tool\$3)))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/01/09 20:16

12	1860420	((semiconductor or (semi adj conductor) or semi-conductor or wafer or IC or (integrated adj circuit) or lot or (micro adj electronic) or microelectronic or memory or (logic adj unit) or microprocessor or process\$3 or fabricat\$3 or produc\$4 or manufactur\$3 or deposit\$3 or etch\$3 or metrology or measur\$3 or tool\$3) with (((process\$3 or cycle or average or mean) near3 (time or rate)) or uniform\$3 or thickness or (critical adj dimension\$3) or CD or variability or target or accura\$4 or defect\$5))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/01/09 20:44
13	4526	(((118/719.ccls. or 29/25.01.ccls. or 427/9.ccls. or 438/5-18.ccls. or 700/19,49,52,99-104,108-111,119-121,123.ccls.) and (((semiconductor or (semi adj conductor) or semi-conductor or wafer or IC or (integrated adj circuit) or lot or (micro adj electronic) or microelectronic or memory or (logic adj unit) or microprocessor) with (process\$3 or fabricat\$3 or produc\$4 or manufactur\$3 or making)))) and (((semiconductor or (semi adj conductor) or semi-conductor or wafer or IC or (integrated adj circuit) or lot or (micro adj electronic) or microelectronic or memory or (logic adj unit) or microprocessor or process\$3 or fabricat\$3 or produc\$4 or manufactur\$3) with (deposit\$3 or etch\$3 or metrology or measur\$3 or tool\$3)))) and (((semiconductor or (semi adj conductor) or semi-conductor or wafer or IC or (integrated adj circuit) or lot or (micro adj electronic) or microelectronic or memory or (logic adj unit) or microprocessor or process\$3 or fabricat\$3 or produc\$4 or manufactur\$3 or deposit\$3 or etch\$3 or metrology or measur\$3 or tool\$3) with (((process\$3 or cycle or average or mean) near3 (time or rate)) or uniform\$3 or thickness or (critical adj dimension\$3) or CD or variability or target or accura\$4 or defect\$5))))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/01/09 20:23
14	1069	700/19,49,52,99-104,108-111,119-121,123.ccls. and (((118/719.ccls. or 29/25.01.ccls. or 427/9.ccls. or 438/5-18.ccls. or 700/19,49,52,99-104,108-111,119-121,123.ccls.) and (((semiconductor or (semi adj conductor) or semi-conductor or wafer or IC or (integrated adj circuit) or lot or (micro adj electronic) or microelectronic or memory or (logic adj unit) or microprocessor) with (process\$3 or fabricat\$3 or produc\$4 or manufactur\$3 or making)))) and (((semiconductor or (semi adj conductor) or semi-conductor or wafer or IC or (integrated adj circuit) or lot or (micro adj electronic) or microelectronic or memory or (logic adj unit) or microprocessor or process\$3 or fabricat\$3 or produc\$4 or manufactur\$3) with (deposit\$3 or etch\$3 or metrology or measur\$3 or tool\$3)))) and (((semiconductor or (semi adj conductor) or semi-conductor or wafer or IC or (integrated adj circuit) or lot or (micro adj electronic) or microelectronic or memory or (logic adj unit) or microprocessor or process\$3 or fabricat\$3 or produc\$4 or manufactur\$3 or deposit\$3 or etch\$3 or metrology or measur\$3 or tool\$3) with (((process\$3 or cycle or average or mean) near3 (time or rate)) or uniform\$3 or thickness or (critical adj dimension\$3) or CD or variability or target or accura\$4 or defect\$5))))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/01/09 20:23
15	560847	((semiconductor or (semi adj conductor) or semi-conductor or wafer) with (process\$3 or fabricat\$3 or production or manufactur\$3))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/01/09 20:40
16	6256	(118/719.ccls. or 29/25.01.ccls. or 427/9.ccls. or 438/5-18.ccls. or 700/19,49,52,99-104,108-111,119-121,123.ccls.) and (((semiconductor or (semi adj conductor) or semi-conductor or wafer) with (process\$3 or fabricat\$3 or production or manufactur\$3))))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/01/09 20:40
17	2140	(((118/719.ccls. or 29/25.01.ccls. or 427/9.ccls. or 438/5-18.ccls. or 700/19,49,52,99-104,108-111,119-121,123.ccls.) and (((semiconductor or (semi adj conductor) or semi-conductor or wafer) with (process\$3 or fabricat\$3 or production or manufactur\$3)))) and ((tool\$3 or chamber or processor) with (deposit\$3 or etch\$3 or metrology or measur\$3 or polish\$3 or lithography or exposure or oxidation or oxidizing or implant\$5 or planariz\$5 or CVD or vapor-deposit\$3 or chemical-vapor or clean\$3))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/01/09 20:50

18	873	((((118/719.ccls. or 29/25.01.ccls. or 427/9.ccls. or 438/5-18.ccls. or 700/19,49,52,99-104,108-111,119-121,123.ccls.) and'(((semiconductor or (semi adj conductor) or semi-conductor or wafer) with (process\$3 or fabricat\$3 or production or manufactur\$3)))) and ((tool\$3 or chamber or processor) with (deposit\$3 or etch\$3 or metrology or measur\$3 or polish\$3 or lithography or exposure or oxidation or oxidizing or implant\$5 or planariz\$5 or CVD or vapor-deposit\$3 or chemical-vapor or clean\$3))) and (chamber with (((process\$3 or cycle or average or mean) near3 (time or rate)) or uniform\$3 or thickness or (critical adj dimension\$3) or CD or variability or target or accura\$4 or defect\$5)))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/01/09 21:03
19	113	700/19,49,52,99-104,108-111,119-121,123.ccls. and (((118/719.ccls. or 29/25.01.ccls. or 427/9.ccls. or 438/5-18.ccls. or 700/19,49,52,99-104,108-111,119-121,123.ccls.) and (((semiconductor or (semi adj conductor) or semi-conductor or wafer) with (process\$3 or fabricat\$3 or production or manufactur\$3)))) and ((tool\$3 or chamber or processor) with (deposit\$3 or etch\$3 or metrology or measur\$3 or polish\$3 or lithography or exposure or oxidation or oxidizing or implant\$5 or planariz\$5 or CVD or vapor-deposit\$3 or chemical-vapor or clean\$3))) and (chamber with (((process\$3 or cycle or average or mean) near3 (time or rate)) or uniform\$3 or thickness or (critical adj dimension\$3) or CD or variability or target or accura\$4 or defect\$5)))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/01/09 20:45
20	1804	((118/719.ccls. or 29/25.01.ccls. or 427/9.ccls. or 438/5-18.ccls. or 700/19,49,52,99-104,108-111,119-121,123.ccls.) and (((semiconductor or (semi adj conductor) or semi-conductor or wafer) with (process\$3 or fabricat\$3 or production or manufactur\$3)))) and ((tool\$3 or chamber or processor) with (deposit\$3 or etch\$3 or metrology or measur\$3)))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/01/09 20:50
21	581	((((118/719.ccls. or 29/25.01.ccls. or 427/9.ccls. or 438/5-18.ccls. or 700/19,49,52,99-104,108-111,119-121,123.ccls.) and (((semiconductor or (semi adj conductor) or semi-conductor or wafer) with (process\$3 or fabricat\$3 or production or manufactur\$3)))) and ((tool\$3 or chamber or processor) with (deposit\$3 or etch\$3 or metrology or measur\$3))) and (chamber near5 (((process\$3 or cycle or average or mean) near3 (time or rate)) or uniform\$3 or thickness or (critical adj dimension\$3) or CD or variability or target or accura\$4 or defect\$5)))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/01/09 20:51
22	263	(((((118/719.ccls. or 29/25.01.ccls. or 427/9.ccls. or 438/5-18.ccls. or 700/19,49,52,99-104,108-111,119-121,123.ccls.) and (((semiconductor or (semi adj conductor) or semi-conductor or wafer) with (process\$3 or fabricat\$3 or production or manufactur\$3)))) and ((tool\$3 or chamber or processor) with (deposit\$3 or etch\$3 or metrology or measur\$3))) and (chamber near5 (((process\$3 or cycle or average or mean) near3 (time or rate)) or uniform\$3 or thickness or (critical adj dimension\$3) or CD or variability or target or accura\$4 or defect\$5))) and (@pd<=20000813)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/01/09 21:10
23	439	((118/719.ccls. or 29/25.01.ccls. or 427/9.ccls. or 438/5-18.ccls. or 700/19,49,52,99-104,108-111,119-121,123.ccls.) and (((semiconductor or (semi adj conductor) or semi-conductor or wafer) with (process\$3 or fabricat\$3 or production or manufactur\$3)))) and (chamber with (((process\$3 or cycle or average or mean) near3 (time or rate)) or (defect\$5 near3 rate) or ((uniform\$3 or variab\$5) near3 (thickness or (critical adj dimension\$3) or CD or target or value)) or ((accura\$4 or precision) near3 process\$3)))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/01/09 21:37
24	167	((((118/719.ccls. or 29/25.01.ccls. or 427/9.ccls. or 438/5-18.ccls. or 700/19,49,52,99-104,108-111,119-121,123.ccls.) and (((semiconductor or (semi adj conductor) or semi-conductor or wafer) with (process\$3 or fabricat\$3 or production or manufactur\$3)))) and (chamber with (((process\$3 or cycle or average or mean) near3 (time or rate)) or (defect\$5 near3 rate) or ((uniform\$3 or variab\$5) near3 (thickness or (critical adj dimension\$3) or CD or target or value)) or ((accura\$4 or precision) near3 process\$3)))) and (@pd<=20000813)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/01/09 21:37

25	23	(((118/719.ccls. or 29/25.01.ccls. or 427/9.ccls. or 438/5-18.ccls. or 700/19,49,52,99-104,108-111,119-121,123.ccls.) and (((semiconductor or (semi adj conductor) or semi-conductor or wafer) with (process\$3 or fabricat\$3 or production or manufactur\$3)))) and (chamber with (((process\$3 or cycle or average or mean) near3 (time or rate)) or (defect\$5 near3 rate) or ((uniform\$3 or variab\$5) near3 (thickness or (critical adj dimension\$3) or CD or target or value)) or ((accura\$4 or precision) near3 process\$3)))) and (@pd<=20000813)) and (software)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/01/09 21:34
26	272	(((118/719.ccls. or 29/25.01.ccls. or 427/9.ccls. or 438/5-18.ccls. or 700/19,49,52,99-104,108-111,119-121,123.ccls.) and (((semiconductor or (semi adj conductor) or semi-conductor or wafer) with (process\$3 or fabricat\$3 or production or manufactur\$3)))) and (chamber with (((process\$3 or cycle or average or mean) near3 (time or rate)) or (defect\$5 near3 rate) or ((uniform\$3 or variab\$5) near3 (thickness or (critical adj dimension\$3) or CD or target or value)) or ((accura\$4 or precision) near3 process\$3)))) not (((118/719.ccls. or 29/25.01.ccls. or 427/9.ccls. or 438/5-18.ccls. or 700/19,49,52,99-104,108-111,119-121,123.ccls.) and (((semiconductor or (semi adj conductor) or semi-conductor or wafer) with (process\$3 or fabricat\$3 or production or manufactur\$3)))) and (chamber with (((process\$3 or cycle or average or mean) near3 (time or rate)) or (defect\$5 near3 rate) or ((uniform\$3 or variab\$5) near3 (thickness or (critical adj dimension\$3) or CD or target or value)) or ((accura\$4 or precision) near3 process\$3)))) and (@pd<=20000813))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/01/09 21:34
27	55	(((118/719.ccls. or 29/25.01.ccls. or 427/9.ccls. or 438/5-18.ccls. or 700/19,49,52,99-104,108-111,119-121,123.ccls.) and (((semiconductor or (semi adj conductor) or semi-conductor or wafer) with (process\$3 or fabricat\$3 or production or manufactur\$3)))) and (chamber with (((process\$3 or cycle or average or mean) near3 (time or rate)) or (defect\$5 near3 rate) or ((uniform\$3 or variab\$5) near3 (thickness or (critical adj dimension\$3) or CD or target or value)) or ((accura\$4 or precision) near3 process\$3)))) not (((118/719.ccls. or 29/25.01.ccls. or 427/9.ccls. or 438/5-18.ccls. or 700/19,49,52,99-104,108-111,119-121,123.ccls.) and (((semiconductor or (semi adj conductor) or semi-conductor or wafer) with (process\$3 or fabricat\$3 or production or manufactur\$3)))) and (chamber with (((process\$3 or cycle or average or mean) near3 (time or rate)) or (defect\$5 near3 rate) or ((uniform\$3 or variab\$5) near3 (thickness or (critical adj dimension\$3) or CD or target or value)) or ((accura\$4 or precision) near3 process\$3)))) and (@pd<=20000813)) and (applied adj materials).as.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/01/09 21:37
28	513	(118/719.ccls. or 29/25.01.ccls. or 427/9.ccls. or 438/5-18.ccls. or 700/19,49,52,99-104,108-111,119-121,123.ccls.) and (chamber with (((process\$3 or cycle or average or mean) near3 (time or rate)) or (defect\$5 near3 rate) or ((uniform\$3 or variab\$5) near3 (thickness or (critical adj dimension\$3) or CD or target or value)) or ((accura\$4 or precision) near3 process\$3)))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/01/09 21:51
29	78	((118/719.ccls. or 29/25.01.ccls. or 427/9.ccls. or 438/5-18.ccls. or 700/19,49,52,99-104,108-111,119-121,123.ccls.) and (chamber with (((process\$3 or cycle or average or mean) near3 (time or rate)) or (defect\$5 near3 rate) or ((uniform\$3 or variab\$5) near3 (thickness or (critical adj dimension\$3) or CD or target or value)) or ((accura\$4 or precision) near3 process\$3)))) and (applied adj materials).as.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/01/09 21:37
30	23	(((118/719.ccls. or 29/25.01.ccls. or 427/9.ccls. or 438/5-18.ccls. or 700/19,49,52,99-104,108-111,119-121,123.ccls.) and (chamber with (((process\$3 or cycle or average or mean) near3 (time or rate)) or (defect\$5 near3 rate) or ((uniform\$3 or variab\$5) near3 (thickness or (critical adj dimension\$3) or CD or target or value)) or ((accura\$4 or precision) near3 process\$3)))) and (applied adj materials).as.) and (@pd<=20000813)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/01/09 21:37

31	55	(((118/719.ccls. or 29/25.01.ccls. or 427/9.ccls. or 438/5-18.ccls. or 700/19,49,52,99-104,108-111,119-121,123.ccls.) and (chamber with (((process\$3 or cycle or average or mean) near3 (time or rate)) or (defect\$5 near3 rate) or ((uniform\$3 or variab\$5) near3 (thickness or (critical adj dimension\$3) or CD or target or value)) or ((accura\$4 or precision) near3 process\$3)))) and (applied adj materials).as.) not (((118/719.ccls. or 29/25.01.ccls. or 427/9.ccls. or 438/5-18.ccls. or 700/19,49,52,99-104,108-111,119-121,123.ccls.) and (chamber with (((process\$3 or cycle or average or mean) near3 (time or rate)) or (defect\$5 near3 rate) or ((uniform\$3 or variab\$5) near3 (thickness or (critical adj dimension\$3) or CD or target or value)) or ((accura\$4 or precision) near3 process\$3)))) and (applied adj materials).as.) and (@pd<=20000813)))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/01/09 21:38
32	55	(((118/719.ccls. or 29/25.01.ccls. or 427/9.ccls. or 438/5-18.ccls. or 700/19,49,52,99-104,108-111,119-121,123.ccls.) and (chamber with (((process\$3 or cycle or average or mean) near3 (time or rate)) or (defect\$5 near3 rate) or ((uniform\$3 or variab\$5) near3 (thickness or (critical adj dimension\$3) or CD or target or value)) or ((accura\$4 or precision) near3 process\$3)))) and (applied adj materials).as.) not (((118/719.ccls. or 29/25.01.ccls. or 427/9.ccls. or 438/5-18.ccls. or 700/19,49,52,99-104,108-111,119-121,123.ccls.) and (chamber with (((process\$3 or cycle or average or mean) near3 (time or rate)) or (defect\$5 near3 rate) or ((uniform\$3 or variab\$5) near3 (thickness or (critical adj dimension\$3) or CD or target or value)) or ((accura\$4 or precision) near3 process\$3)))) and (applied adj materials).as.) and (@pd<=20000813))) and (chamber with (((process\$3 or cycle or average or mean) near3 (time or rate)) or (defect\$5 near3 rate) or ((uniform\$3 or variab\$5) near3 (thickness or (critical adj dimension\$3) or CD or target or value)) or ((accura\$4 or precision) near3 process\$3))))).clm	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/01/09 22:23
33	12	(((118/719.ccls. or 29/25.01.ccls. or 427/9.ccls. or 438/5-18.ccls. or 700/19,49,52,99-104,108-111,119-121,123.ccls.) and (chamber with (((process\$3 or cycle or average or mean) near3 (time or rate)) or (defect\$5 near3 rate) or ((uniform\$3 or variab\$5) near3 (thickness or (critical adj dimension\$3) or CD or target or value)) or ((accura\$4 or precision) near3 process\$3)))) and (applied adj materials).as.) not (((118/719.ccls. or 29/25.01.ccls. or 427/9.ccls. or 438/5-18.ccls. or 700/19,49,52,99-104,108-111,119-121,123.ccls.) and (chamber with (((process\$3 or cycle or average or mean) near3 (time or rate)) or (defect\$5 near3 rate) or ((uniform\$3 or variab\$5) near3 (thickness or (critical adj dimension\$3) or CD or target or value)) or ((accura\$4 or precision) near3 process\$3)))) and (applied adj materials).as.) and (@pd<=20000813))) and (chamber with (((process\$3 or cycle or average or mean) near3 (time or rate)) or (defect\$5 near3 rate) or ((uniform\$3 or variab\$5) near3 (thickness or (critical adj dimension\$3) or CD or target or value)) or ((accura\$4 or precision) near3 process\$3))))).clm	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/01/09 21:52
38	55	(((118/719.ccls. or 29/25.01.ccls. or 427/9.ccls. or 438/5-18.ccls. or 700/19,49,52,99-104,108-111,119-121,123.ccls.) and (chamber with (((process\$3 or cycle or average or mean) near3 (time or rate)) or (defect\$5 near3 rate) or ((uniform\$3 or variab\$5) near3 (thickness or (critical adj dimension\$3) or CD or target or value)) or ((accura\$4 or precision) near3 process\$3)))) and (applied adj materials).as.) not (((118/719.ccls. or 29/25.01.ccls. or 427/9.ccls. or 438/5-18.ccls. or 700/19,49,52,99-104,108-111,119-121,123.ccls.) and (chamber with (((process\$3 or cycle or average or mean) near3 (time or rate)) or (defect\$5 near3 rate) or ((uniform\$3 or variab\$5) near3 (thickness or (critical adj dimension\$3) or CD or target or value)) or ((accura\$4 or precision) near3 process\$3)))) and (applied adj materials).as.) and (@pd<=20000813))) and (chamber with (((process\$3 or cycle or average or mean) near3 (time or rate)) or (defect\$5 near3 rate) or ((uniform\$3 or variab\$5) near3 (thickness or (critical adj dimension\$3) or CD or target or value or parameter)) or ((accura\$4) near3 (process\$3 or tool or chamber))))).clm	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/01/09 22:24

39	1582	(chamber with (((process\$3 or cycle or average or mean) near3 (time or rate)) or (defect\$5 near3 rate) or ((uniform\$3 or variab\$5) near3 (thickness or (critical adj dimension\$3) or CD or target or value or parameter)) or ((accura\$4) near3 (process\$3 or tool or chamber))))).clm.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/01/09 22:28
40	74	((chamber with (((process\$3 or cycle or average or mean) near3 (time or rate)) or (defect\$5 near3 rate) or ((uniform\$3 or variab\$5) near3 (thickness or (critical adj dimension\$3) or CD or target or value or parameter)) or ((accura\$4) near3 (process\$3 or tool or chamber))))).clm.) and (118/719.ccls. or 29/25.01.ccls. or 427/9.ccls. or 438/5-18.ccls. or 700/19,49,52,99-104,108-111,119-121,123.ccls.)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/01/09 22:31
41	54	(chamber with (determin\$5 or comput\$5 or calculat\$3) with (((process\$3 or cycle or average or mean) near3 (time or rate)) or (defect\$5 near3 rate) or ((uniform\$3 or variab\$5) near3 (thickness or (critical adj dimension\$3) or CD or target or value or parameter)) or ((accura\$4) near3 (process\$3 or tool or chamber))))).clm. and software	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/01/09 22:31
42	18	((chamber with (determin\$5 or comput\$5 or calculat\$3) with (((process\$3 or cycle or average or mean) near3 (time or rate)) or (defect\$5 near3 rate) or ((uniform\$3 or variab\$5) near3 (thickness or (critical adj dimension\$3) or CD or target or value or parameter)) or ((accura\$4) near3 (process\$3 or tool or chamber))))).clm. and software) and (118/719.ccls. or 29/25.01.ccls. or 427/9.ccls. or 438/5-18.ccls. or 700/19,49,52,99-104,108-111,119-121,123.ccls.)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/01/09 22:31
43	153	(chamber with (determin\$5 or comput\$5 or calculat\$3) with (((process\$3 or cycle or average or mean) near3 (time or rate)) or (defect\$5 near3 rate) or ((uniform\$3 or variab\$5) near3 (thickness or (critical adj dimension\$3) or CD or target or value or parameter)) or ((accura\$4) near3 (process\$3 or tool or chamber))))).clm.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/01/09 22:31
45	36	((chamber with (determin\$5 or comput\$5 or calculat\$3) with (((process\$3 or cycle or average or mean) near3 (time or rate)) or (defect\$5 near3 rate) or ((uniform\$3 or variab\$5) near3 (thickness or (critical adj dimension\$3) or CD or target or value or parameter)) or ((accura\$4) near3 (process\$3 or tool or chamber))))).clm. and software) not (((chamber with (determin\$5 or comput\$5 or calculat\$3) with (((process\$3 or cycle or average or mean) near3 (time or rate)) or (defect\$5 near3 rate) or ((uniform\$3 or variab\$5) near3 (thickness or (critical adj dimension\$3) or CD or target or value or parameter)) or ((accura\$4) near3 (process\$3 or tool or chamber))))).clm. and software) and (118/719.ccls. or 29/25.01.ccls. or 427/9.ccls. or 438/5-18.ccls. or 700/19,49,52,99-104,108-111,119-121,123.ccls.)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/01/09 22:32
44	25	((chamber with (determin\$5 or comput\$5 or calculat\$3) with (((process\$3 or cycle or average or mean) near3 (time or rate)) or (defect\$5 near3 rate) or ((uniform\$3 or variab\$5) near3 (thickness or (critical adj dimension\$3) or CD or target or value or parameter)) or ((accura\$4) near3 (process\$3 or tool or chamber))))).clm.) and (118/719.ccls. or 29/25.01.ccls. or 427/9.ccls. or 438/5-18.ccls. or 700/19,49,52,99-104,108-111,119-121,123.ccls.)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/01/09 22:46
46	7	((chamber with (determin\$5 or comput\$5 or calculat\$3) with (((process\$3 or cycle or average or mean) near3 (time or rate)) or (defect\$5 near3 rate) or ((uniform\$3 or variab\$5) near3 (thickness or (critical adj dimension\$3) or CD or target or value or parameter)) or ((accura\$4) near3 (process\$3 or tool or chamber))))).clm.) and (118/719.ccls. or 29/25.01.ccls. or 427/9.ccls. or 438/5-18.ccls. or 700/19,49,52,99-104,108-111,119-121,123.ccls.) not ((chamber with (determin\$5 or comput\$5 or calculat\$3) with (((process\$3 or cycle or average or mean) near3 (time or rate)) or (defect\$5 near3 rate) or ((uniform\$3 or variab\$5) near3 (thickness or (critical adj dimension\$3) or CD or target or value or parameter)) or ((accura\$4) near3 (process\$3 or tool or chamber))))).clm. and software)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/01/09 22:46
-	2	20030029383.pn.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/01/09 20:06